40V P-Channel MOSFET

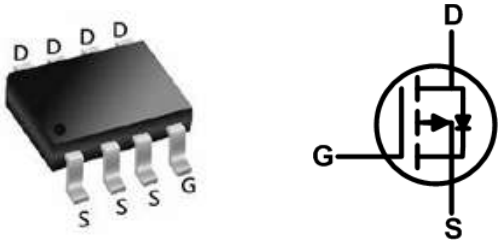
Features

- Advanced Trench MOS Technology
- Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available

Applications

- Load Switches
- Hard Switching and High Speed Circuit

SOP8 Pin Configuration



Product Summary

BVDSS	RDSON	ID
-40V	22mΩ	-9.8A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	-9.8	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	-7.8	A
I_{DM}	Pulsed Drain Current[2]	-40	A
EAS	Single Pulse Avalanche Energy[3]	31	mJ
I_{AS}	Avalanche Current	-25	A
P_D@T_A=25℃	Total Power Dissipation[4]	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	75	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1](t≦10S)	---	40	℃/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-8A	---	17	22	mΩ
		V_{GS}=-4.5V , I_D=-6A	---	24	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-1.6	-2.2	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-32V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-32V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	10	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-20V , V_{GS}=-4.5V , I_D=-8A	---	19.5	---	nC
Q_{gs}	Gate-Source Charge		---	6.1	---	
Q_{gd}	Gate-Drain Charge		---	6.6	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-20V , V_{GS}=-10V , R_G=6Ω, I_D=-1A	---	13	---	ns
T_r	Rise Time		---	24	---	
$T_{d(off)}$	Turn-Off Delay Time		---	28	---	
T_f	Fall Time		---	23	---	
C_{iss}	Input Capacitance	V_{DS}=-20V , V_{GS}=0V , f=1MHz	---	2370	---	pF
C_{oss}	Output Capacitance		---	189	---	
C_{rss}	Reverse Transfer Capacitance		---	160	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1]	V_G=V_D=0V , Force Current	---	---	-9.8	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AS}=-25A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

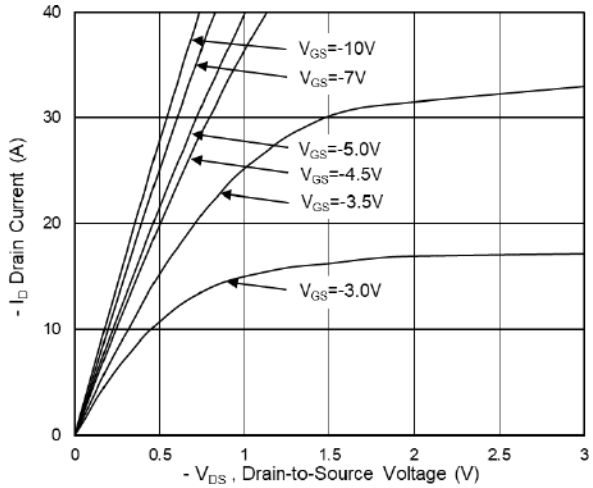


Fig.1 Typical Output Characteristics

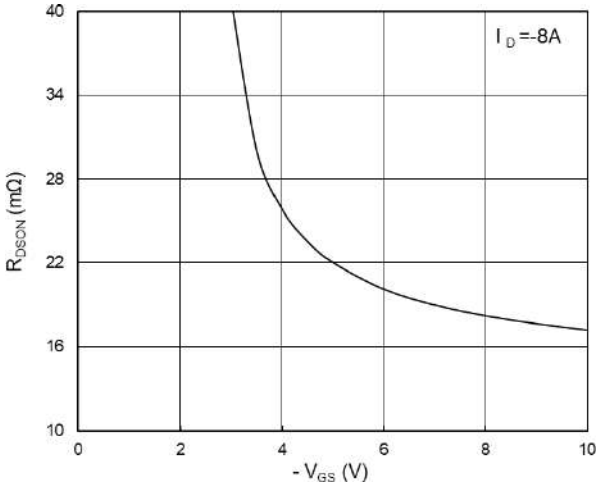


Fig.2 On-Resistance vs G-S Voltage

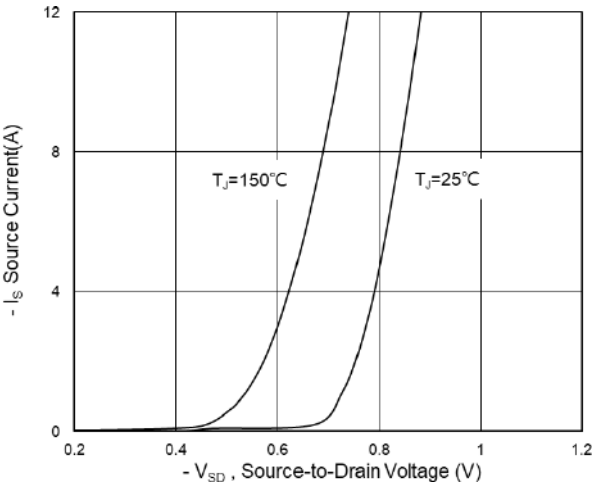


Fig.3 Source Drain Forward Characteristics

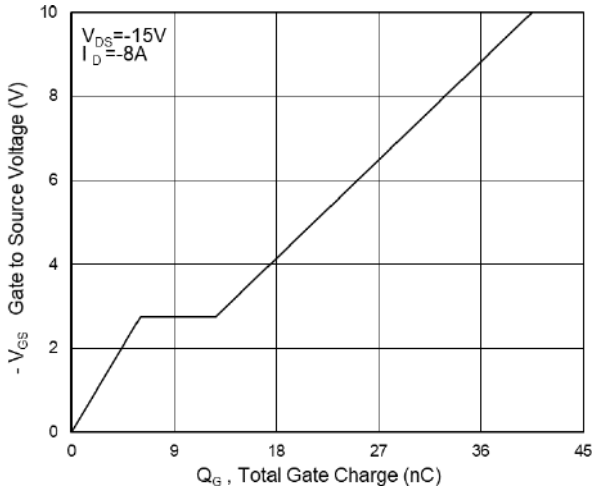


Fig.4 Gate-Charge Characteristics

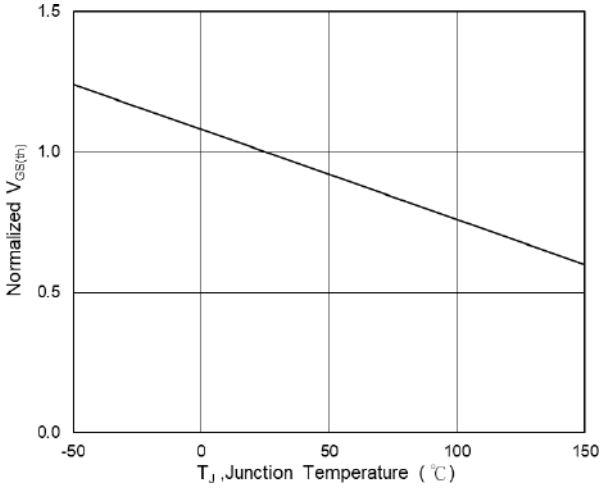


Fig.5 Normalized $V_{GS(th)}$ vs T_J

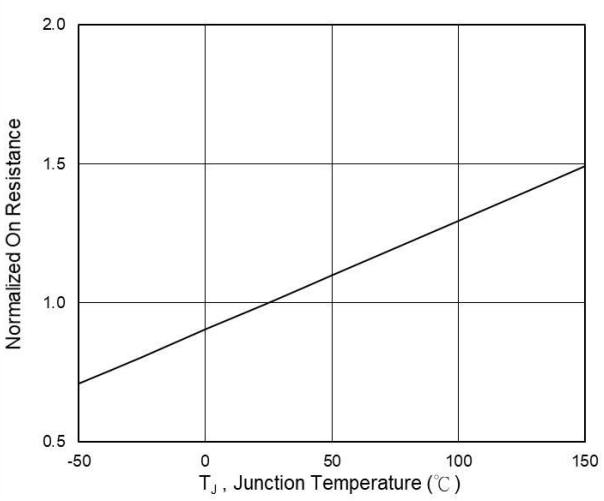


Fig.6 Normalized R_{DSON} vs T_J

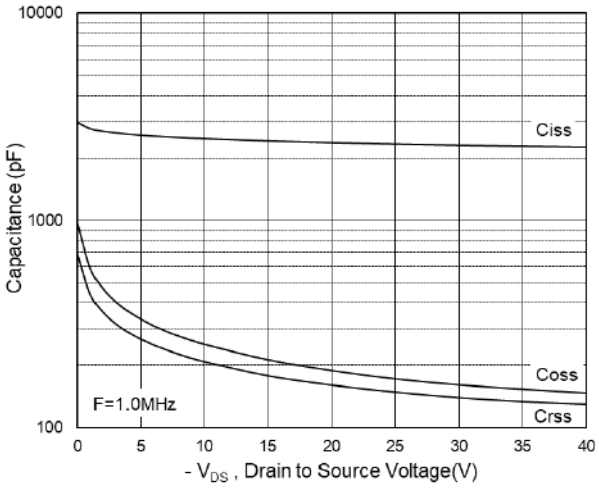


Fig.7 Capacitance

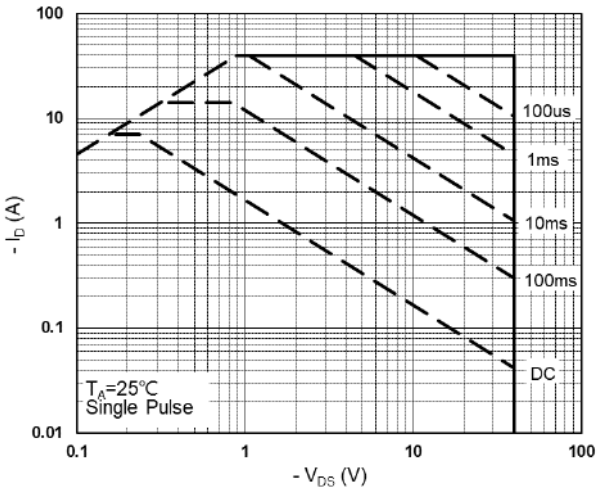


Fig.8 Safe Operating Area

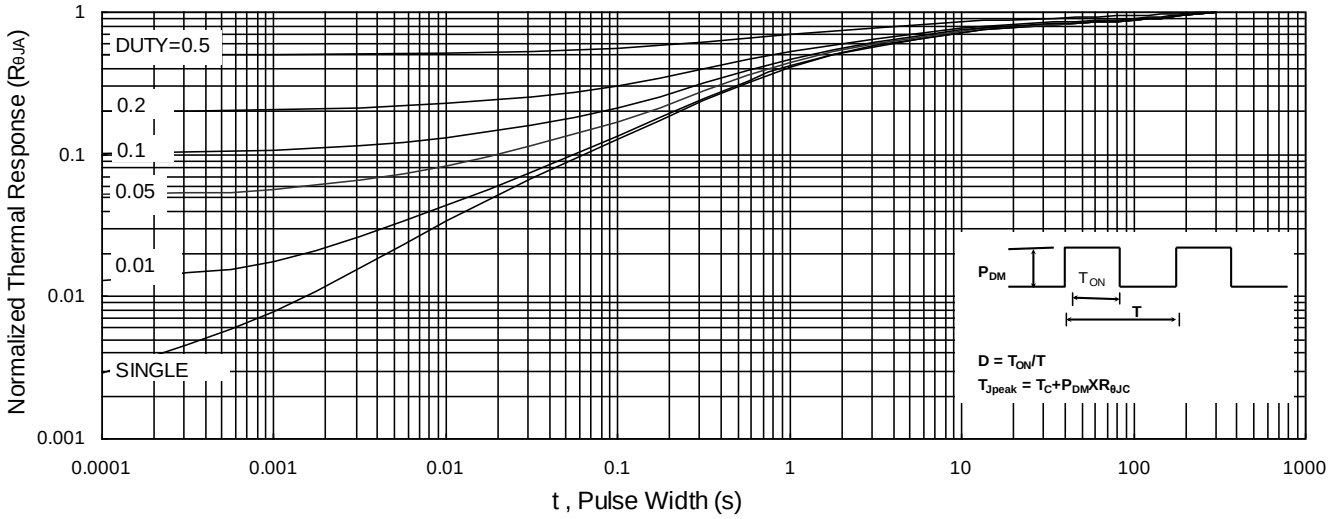


Fig.9 Normalized Maximum Transient Thermal Impedance

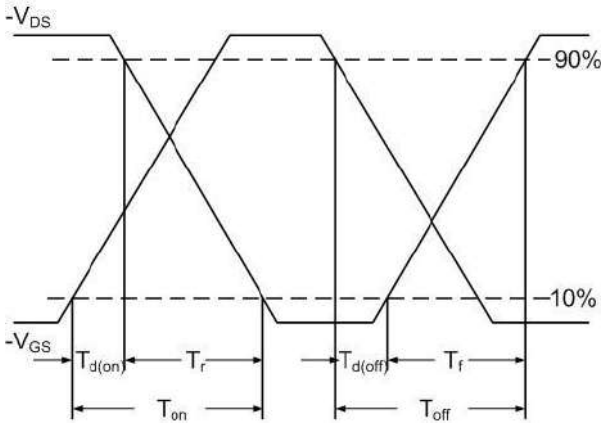


Fig.10 Switching Time Waveform

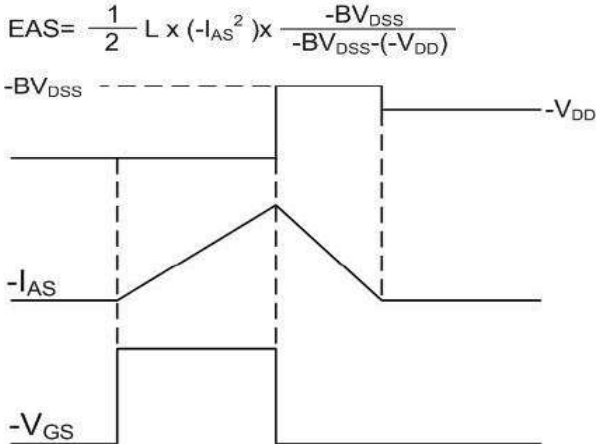


Fig.11 Unclamped Inductive Switching Waveform